

ANGULAR DEPENDENCE OF MAGNETORESISTANCE OF FILLED WITH IRON CARBON NANOTUBES

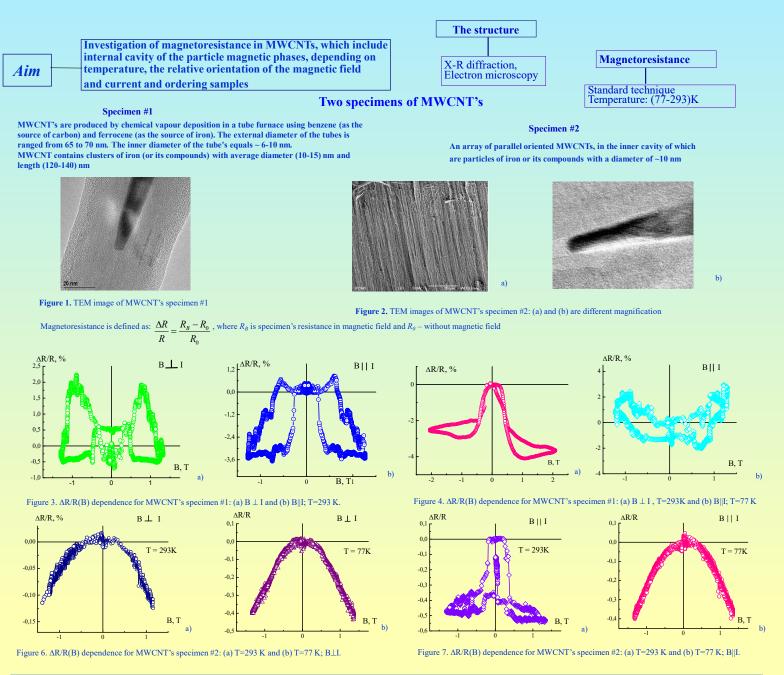


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Two mechanisms of magnetoresistance in layered or clustered systems with alternating magnetic and nonmagnetic layers or magnetic clusters are in a nonmagnetic matrix:

- 1. Giant magnetoresistance mechanism (GM). A characteristic feature of GM is a hysteresis phenomenon in the case of magnetoresistance dependence on magnetic field.
- 2. Anisotropic magnetoresistance (AM). A characteristic feature of AM is a dependent of sign magnetoresistance on the relative orientation of the magnetic field M and current I: $R(\theta_{M,I}) = R_0 + R_A \cdot \cos^2(\theta_{M,I})$, $R_A \equiv R_{\parallel} R_{\perp}$.
- 3. Magnetoresistance of MWCNT's filled with iron and its compounds strongly depends on the structure of CNT and their mutual orientation, and also structural and morphological state of the magnetic phase. For partially oriented Fe-MWCNT's the magnetoresistance is determined by a combination of two mechanisms, namely, GM and AM. For array-oriented Fe-MWCNT's in mutually perpendicular orientation of the magnetic field and current a principal mechanism is the localization magnetoresistance mechanism, and in mutual parallel orientation of the magnetic field and current a GM effect.